

SEMITOP[®]4

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SK 35 DGDL 126 T

Preliminary Data

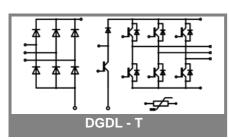
Features

- One screw mounting module
- Fully compatible with SEMITOP[®]1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology free-wheeling diode
- Integrated NTC temperature sensor

Typical Applications*

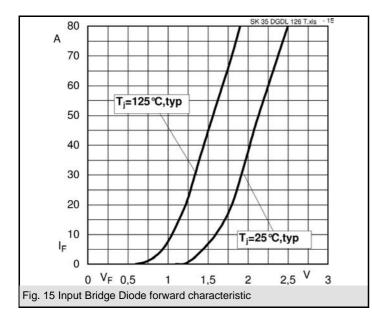
- Inverter up to 19 kVA
- Typ. motor power 7,5 kW

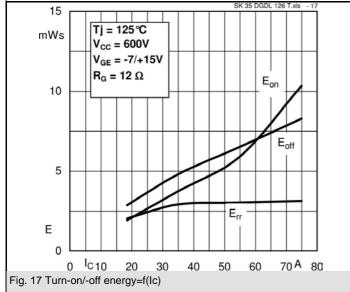
1) $V_{CE,sat}$, V_F = chip level value

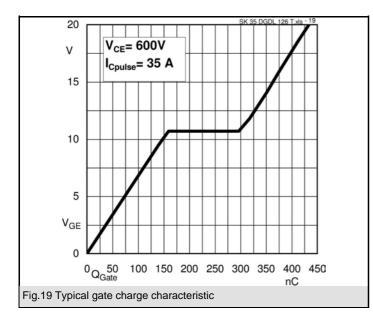


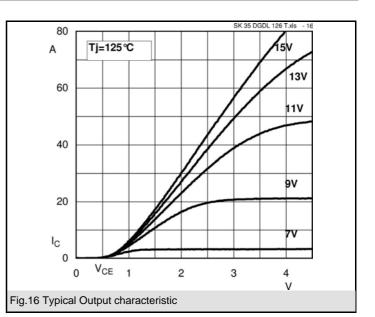
Absolute Maximum Ratings		Ts = 25 °C, unless otherwise	Ts = 25 °C, unless otherwise specified					
Symbol	Conditions	Values	Units					
IGBT - Inverter, Chopper								
V _{CES}		1200	V					
I _C	T _s = 25 (70) °C	52 (40)	А					
I _{CRM}	I_{CRM} = 2 x I_{Cnom} , t_p = 1 ms	70	A					
V _{GES}		± 20	V					
Т _ј		-40 +150	°C					
Diode -	Inverter, Chopper							
I _F	T _s = 25 (70) °C	38 (29)	A					
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 ms$	70	A					
T _j		-40 +150	°C					
Rectifie	er		I					
V _{RRM}		1600	V					
I _F	T _s = 70 °C	35	A					
I _{FSM} / I _{TSM}	t _p = 10 ms , sin 180 ° ,T _i = 25 °C	370	A					
l ² t	t _p = 10 ms , sin 180 ° ,T _i = 25 °C	680	A²s					
T _j		-40 +150	°C					
T _{sol}	Terminals, 10 s	260	°C					
T _{stg}		-40 +125	°C					
V _{isol}	AC, 1 min. / 1 s	2500 / 3000	V					
	· ·		•					
Characteristics Ts = 25 °C, unless otherwise specified								
Symbol	Conditions	min typ may	c Unite					

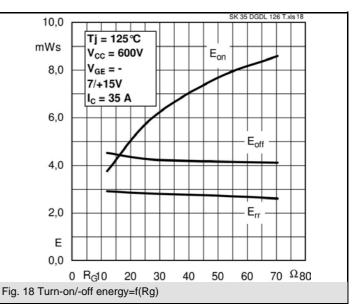
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inv	verter				
V _{CEsat}	I _C = 35 A, T _i = 25 (125) °C		1,7 (2)	2,1 (2,4)	V
V _{GE(th)}	$V_{GE} = V_{CE}, I_{C} = 1,5 \text{ mA}$	5	5,8	6,5	V
V _{CE(TO)}	T _i = 25 °C (125) °C		1 (0,9)	1,2 (1,1)	V
r _T	T _i = 25 °C (125) °C		20 (31)	26 (37)	mΩ
C _{ies}	V _{CE} = 25 V _{GE} = 0 V, f = 1 MHz		2,5		nF
C _{oes}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,13		nF
C _{res}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,11		nF
R _{th(j-s)}	per IGBT		0,75		K/W
t _{d(on)}	under following conditions		99		ns
t _r	V_{CC} = 600 V, V_{GE} = ± 15 V		25		ns
t _{d(off)}	I _C = 35 A, T _j = 125 °C		468		ns
t,	$R_{Gon} = R_{Goff} = 12 \Omega$		89		ns
E _{on}	inductive load		3,7		mJ
E _{off}			4,8		mJ
Diode - Ir	verter,Chopper				
V _F = V _{EC}	I _F = 20 A, T _i = 25(125) °C		1,5 (1,5)	1,77 (1,77)	V
V _(TO)	T _i = 25 °C (125) °C		(0,92)		V
r _T	T _i = 25 °C (125) °C		(27,7)		mΩ
R _{th(j-s)}	per diode		1,5		K/W
I _{RRM}	under following conditions		58		Α
Q _{rr}	I _F = 35 A, V _R = 600 V		9		μC
E _{rr}	V _{GE} = 0 V, T _j = 125 °C		3		mJ
	di _{F/dt} = 1400 A/µs				
Diode - R	ectifier				
V _F	I _F = 25 A, T _i = 25() °C		1,1		V
V _(TO)	T _i = 150 °C		0,8		V
r _T	T _i = 150 °C		13		mΩ
R _{th(j-s)}	per diode		1,25		K/W
	tur sensor				
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω
Mechanic	al data				
w			60		g
M _s	Mounting torque	2,5		2,75	Nm

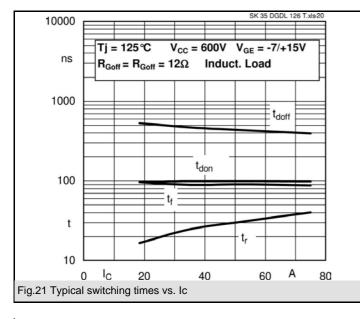


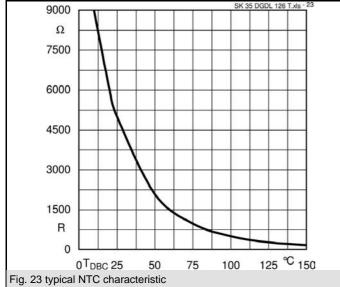


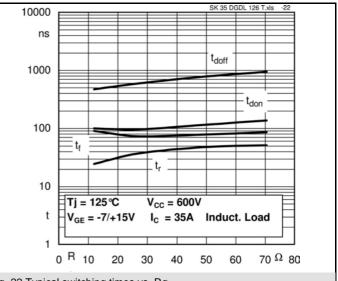


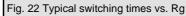


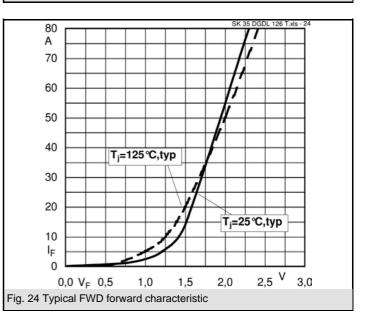






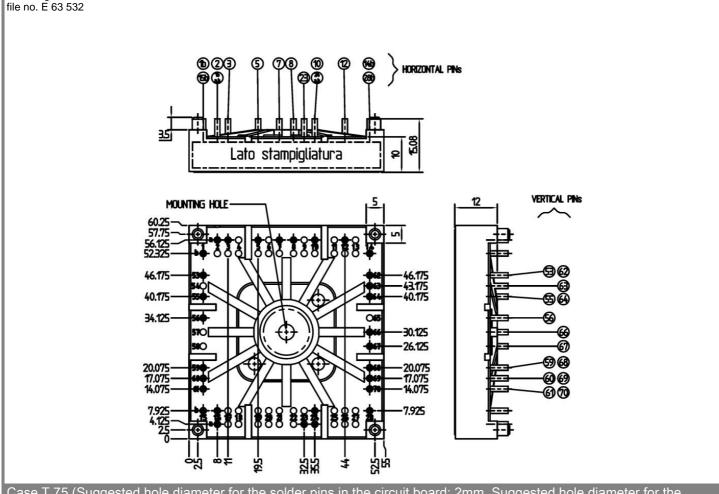


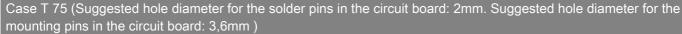


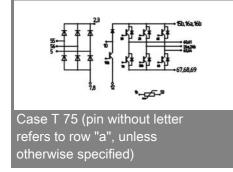


UL recognized

Dimensions in mm







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.